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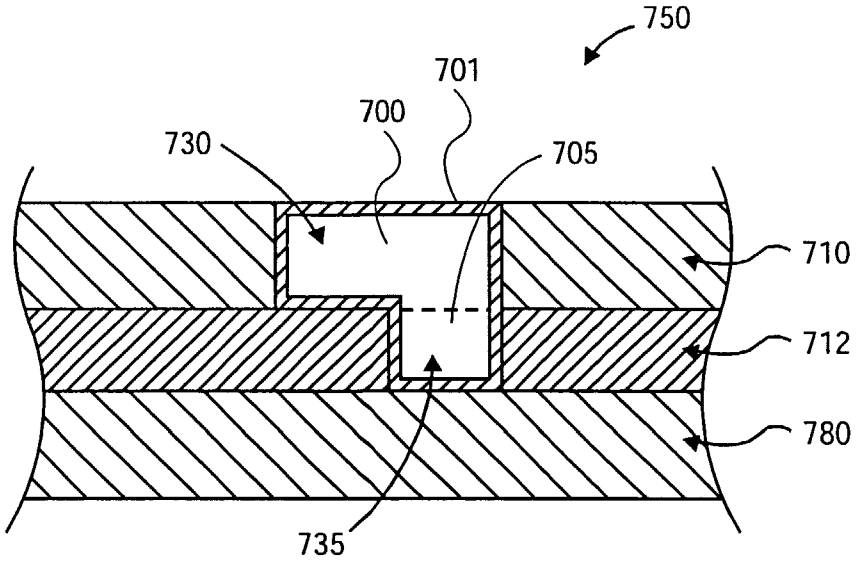
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(54) Title: DOPANT INTERFACE FORMATION OF AN INTERCONNECT



(57) Abstract: Formation of an interconnect circuit feature having e.g. copper as a metal and bismuth as an electropositive dopant. The interconnect feature may comprise an accumulation of the electropositive dopant at interface boundaries (701) of the interconnect feature to reduce electromigration of the metal during operation. A method may comprise heating the interconnect feature to drive a portion of the electropositive dopant to the interfaces.

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